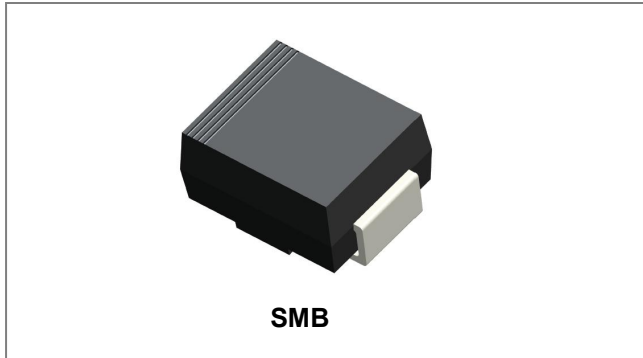


S3AB THRU S3MB 3.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: SMB molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.09 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristic	Symbol	S3AB	S3BB	S3DB	S3GB	S3JB	S3KB	S3MB	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Average forward rectified output current @T _L = 75°C	I_O	3.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	100							A
Forward Voltage @I _F = 3.0A	V_{FM}	1.20							V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 125°C	I_{RM}	5.0 250							μA
Reverse recovery time (Note 1)	t_{rr}	2.5							μs
Typical Junction Capacitance (Note 2)	C_J	60							pF
Typical Thermal Resistance (Note 3)	$R_{\theta JL}$	13							K/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150							°C

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A, Irr=0.25A
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. Mounted on P.C.B. with 8.0mm² land areas.

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Ratings and Characteristics Curves

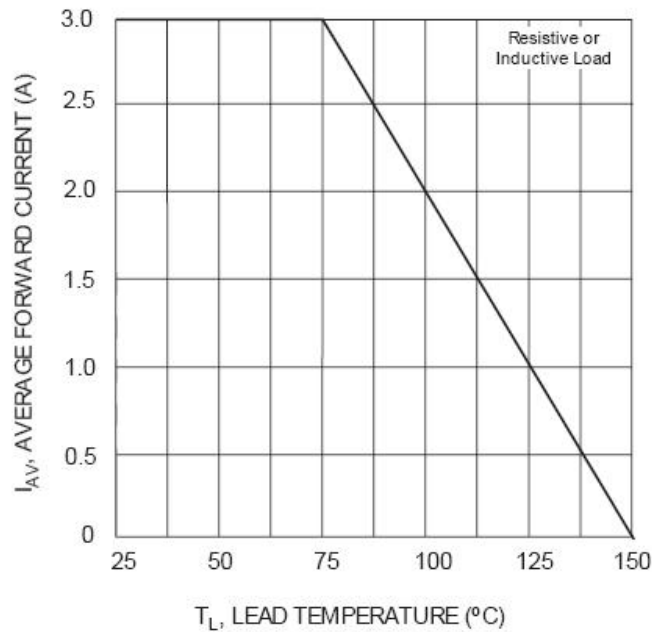


Fig. 1 Forward Current Derating Curve

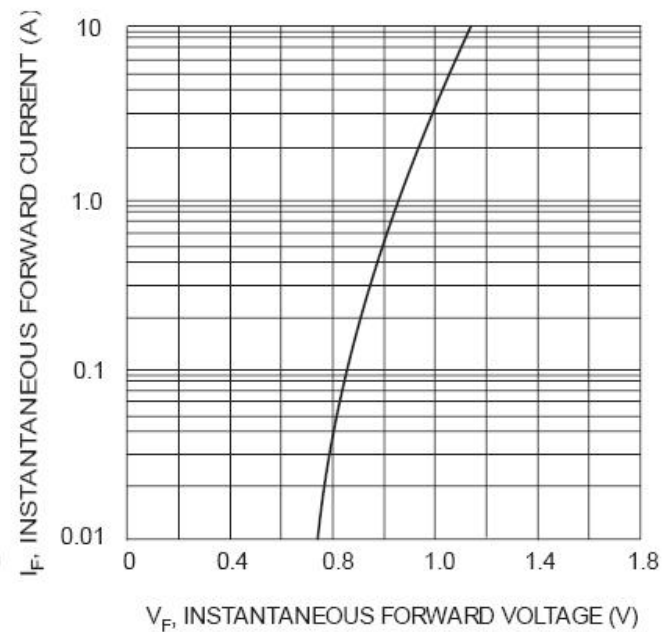


Fig. 2 Typical Forward Characteristics

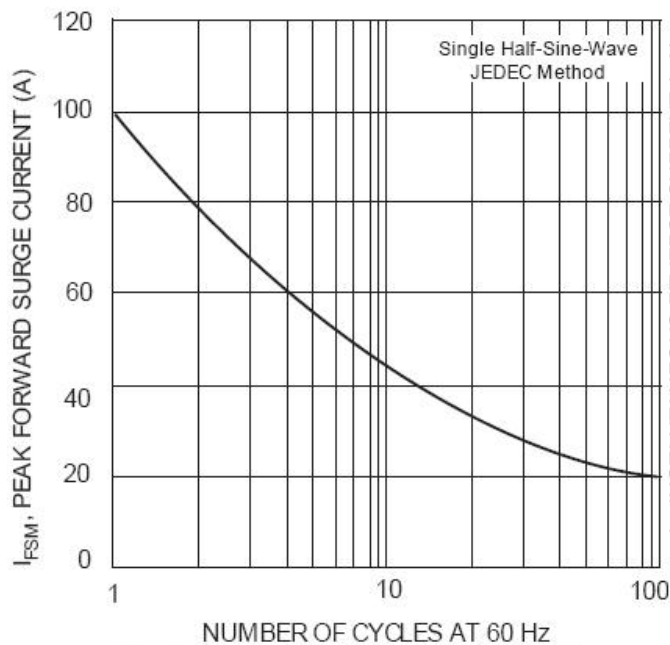


Fig. 3 Forward Surge Current Derating Curve

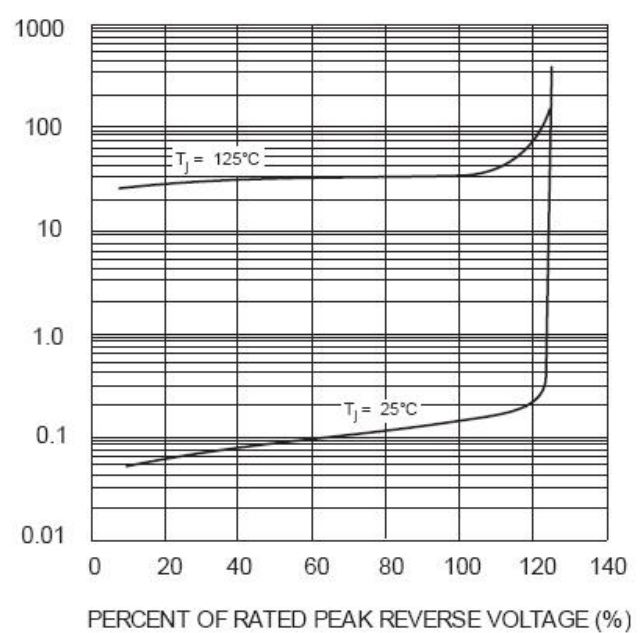
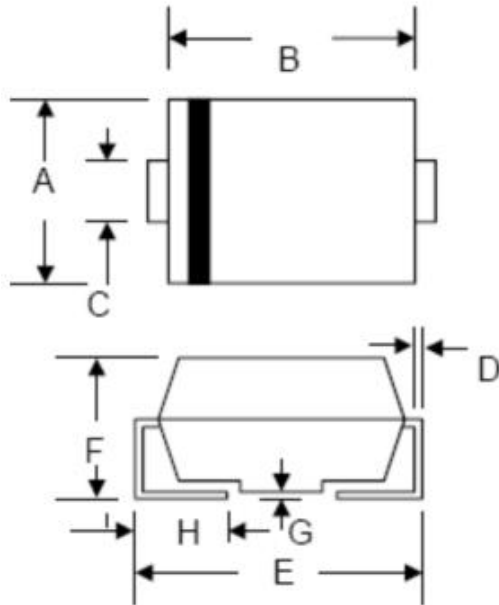


Fig. 4 Typical Reverse Characteristics

Mechanical Dimensions SMB



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.80	2.20	0.071	0.087
D	0.152	0.305	0.006	0.012
E	4.80	5.59	0.189	0.220
F	2.10	2.60	0.083	0.102
G	0.051	0.203	0.002	0.008
H	0.76	1.52	0.030	0.060

Ordering Information

Device	Package	Shipping
S3AB-S3MB	SMB(Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

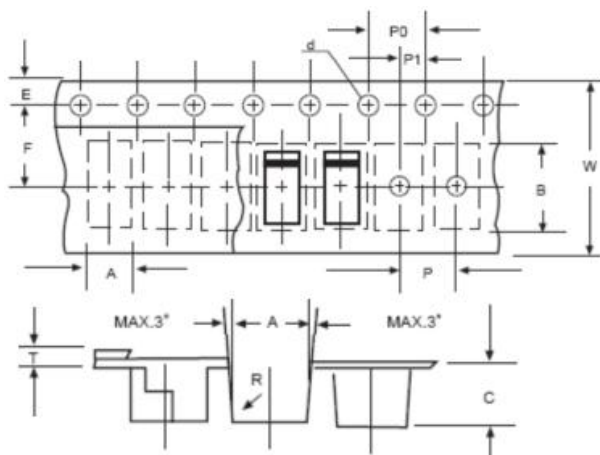


Where XXXXX is YYWWL

S3AB = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification SMB



SYMBOL	Millimeters	
	Min.	Max.
A	3.99	4.19
B	5.72	5.92
C	3.23	3.43
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	7.90	8.10
P0	3.90	4.10
P1	1.90	2.10
T	-	0.60
W	11.80	12.20

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